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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I <sup>2</sup> C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	40
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 15x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl14z64vft4

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong









Symbol	Description	Min.	Max.	Unit	Notes
V <sub>DD</sub>	Supply voltage	1.71	3.6	V	
V <sub>DDA</sub>	Analog supply voltage	1.71	3.6	V	—
$V_{DD} - V_{DDA}$	V <sub>DD</sub> -to-V <sub>DDA</sub> differential voltage	-0.1	0.1	V	—
$V_{SS} - V_{SSA}$	V <sub>SS</sub> -to-V <sub>SSA</sub> differential voltage	-0.1	0.1	V	—
V <sub>IH</sub>	Input high voltage				—
	• $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 3.6 \text{ V}$	$0.7 \times V_{DD}$	—	V	
	• $1.7 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	$0.75 \times V_{DD}$	_	V	
V <sub>IL</sub>	Input low voltage				_
	• $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 3.6 \text{ V}$	_	$0.35 \times V_{DD}$	V	
	• $1.7 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$		$0.3 \times V_{DD}$	V	
V <sub>HYS</sub>	Input hysteresis	$0.06 \times V_{DD}$	_	V	_
I <sub>ICIO</sub>	IO pin negative DC injection current—single pin • V <sub>IN</sub> < V <sub>SS</sub> –0.3V	-3	_	mA	1
I <sub>ICcont</sub>	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins • Negative current injection	-25		mA	_
V <sub>ODPU</sub>	Open drain pullup voltage level	V <sub>DD</sub>	V <sub>DD</sub>	V	2
V <sub>RAM</sub>	V <sub>DD</sub> voltage required to retain RAM	1.2	_	V	—

#### 2.2.1 Voltage and current operating requirements Table 5. Voltage and current operating requirements

2. Open drain outputs must be pulled to  $V_{DD}$ .

### 2.2.2 LVD and POR operating requirements T

able 6.	V <sub>DD</sub> supply LVD and PO	<b>R</b> operating requirements
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V <sub>POR</sub>	Falling V <sub>DD</sub> POR detect voltage	0.8	1.1	1.5	V	—
V <sub>LVDH</sub>	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	—
	Low-voltage warning thresholds — high range					1

Table continues on the next page ...

<sup>1.</sup> All I/O pins are internally clamped to  $V_{SS}$  through a ESD protection diode. There is no diode connection to  $V_{DD}$ . If  $V_{IN}$ greater than V<sub>IO\_MIN</sub> (= V<sub>SS</sub>-0.3 V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as  $R = (V_{IO MIN} - V_{IN})/|I_{ICIO}|$ .



Symbol	Description	Temp.	Тур.	Мах	Unit	Note
		at 70 °C	5.71	7.75	μA	
		at 85 °C	10	13.54	μA	
		at 105 °C	22.4	30.41	μA	
I <sub>DD_VLLS3</sub>	Very low-leakage stop mode 3 current	at 25 °C	1.22	1.6	μA	—
	at 3.0 V	at 50 °C	2.25	2.31	μA	
		at 70 °C	4.21	5.44	μA	
		at 85 °C	7.37	9.44	μA	
		at 105 °C	16.6	21.76	μA	
IDD_VLLS1	Very low-leakage stop mode 1 current	at 25 °C	0.58	0.94	μA	_
	at 3.0 V	at 50 °C	1.26	1.31	μA	
		at 70 °C	2.53	3.33	μA	
		at 85 °C	4.74	6.1	μA	
		at 105 °C	11.4	15.27	μA	
I <sub>DD_VLLS0</sub>	Very low-leakage stop mode 0 current	at 25 °C	0.31	0.65	μA	_
	(SMC_STOPCTRL[PORPO] = 0) at 3.0	at 50 °C	0.99	1.43	μA	
	v	at 70 °C	2.25	3.01	μA	
		at 85 °C	4.46	5.83	μA	
		at 105 °C	11.13	14.99	μA	
IDD_VLLS0	Very low-leakage stop mode 0 current	at 25 °C	0.12	0.47	μA	7
	(SMC_STOPCTRL[PORPO] = 1) at 3.0	at 50 °C	0.8	1.24	μA	
	·	at 70 °C	2.06	2.81	μA	
		at 85 °C	4.27	5.62	μA	
		at 105 °C	10.93	14.78	μA	

#### Table 9. Power consumption operating behaviors (continued)

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.

- 2. MCG configured for PEE mode. CoreMark benchmark compiled using Keil 4.54 with optimization level 3, optimized for time.
- 3. MCG configured for FEI mode.
- 4. Incremental current consumption from peripheral activity is not included.
- 5. MCG configured for BLPI mode. CoreMark benchmark compiled using IAR 6.40 with optimization level high, optimized for balanced.
- 6. MCG configured for BLPI mode.
- 7. No brownout.

#### Table 10. Low power mode peripheral adders — typical value

Symbol	Description	Temperature (°C)			Unit			
		-40	25	50	70	85	105	
I <sub>IREFSTEN4MHz</sub>	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.	56	56	56	56	56	56	μA

Table continues on the next page...





Symbol	Description			٦	Tempera	ature (°0	C)		Unit
			-40	25	50	70	85	105	
I <sub>IREFSTEN32KHz</sub>	32 kHz internal reference clock Measured by entering STOP n 32 kHz IRC enabled.	(IRC) adder. node with the	52	52	52	52	52	52	μA
I <sub>EREFSTEN4MHz</sub>	External 4 MHz crystal clock a Measured by entering STOP o with the crystal enabled.	dder. r VLPS mode	206	228	237	245	251	258	μA
I <sub>EREFSTEN32KHz</sub>	External 32 kHz crystal clock	VLLS1	440	490	540	560	570	580	nA
	OSC0 CRIEREFSTEN and	VLLS3	440	490	540	560	570	580	
	EREFSTEN] bits. Measured	LLS	490	490	540	560	570	680	
	by entering all modes with the	VLPS	510	560	560	560	610	680	
	crystal enabled.	STOP	510	560	560	560	610	680	
I <sub>CMP</sub>	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.		22	22	22	22	22	22	μA
I <sub>RTC</sub>	RTC peripheral adder measure the device in VLLS1 mode with kHz crystal enabled by means RTC_CR[OSCE] bit and the R for 1 minute. Includes ERCLK3 external crystal) power consum	ed by placing n external 32 of the TC ALARM set 32K (32 kHz nption.	432	357	388	475	532	810	nA
I <sub>UART</sub>	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μA
	115200 baud rate. Includes selected clock source power consumption.	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I <sub>TPM</sub>	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output	MCGIRCLK (4 MHz internal reference clock)	86	86	86	86	86	86	μA
	compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	
I <sub>BG</sub>	Bandgap adder when BGEN b device is placed in VLPx, LLS, mode.	it is set and or VLLSx	45	45	45	45	45	45	μA
I <sub>ADC</sub>	ADC peripheral adder combini measured values at V <sub>DD</sub> and V	ng the / <sub>DDA</sub> by placing	366	366	366	366	366	366	μA

Table 10.	Low power mode	peripheral adders —	<ul> <li>typical value (continued)</li> </ul>
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## 3.1.1 SWD electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

Table 17. SWD full voltage range electricals



Figure 5. Serial wire clock input timing



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
J <sub>acc_pll</sub>	PLL accumulated jitter over 1µs (RMS)					10
	• f <sub>vco</sub> = 48 MHz	—	1350	—	ps	
	• f <sub>vco</sub> = 100 MHz	_	600	_	ps	
D <sub>lock</sub>	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D <sub>unl</sub>	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t <sub>pll_lock</sub>	Lock detector detection time	_		150 × 10 <sup>-6</sup> + 1075(1/ f <sub>pll_ref</sub> )	S	11

#### Table 18. MCG specifications (continued)

- 1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
- 2. The deviation is relative to the factory trimmed frequency at nominal  $V_{DD}$  and 25 °C,  $f_{ints_{ft}}$ .
- 3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
- The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation (Δf<sub>dco\_t</sub>) over voltage and temperature must be considered.
- 5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
- 6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 7. This specification is based on standard deviation (RMS) of period or frequency.
- 8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 9. Excludes any oscillator currents that are also consuming power while PLL is in operation.
- 10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
- 11. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

## **3.3.2 Oscillator electrical specifications**

## 3.3.2.1 Oscillator DC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V <sub>DD</sub>	Supply voltage	1.71	—	3.6	V	
IDDOSC	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	_	500	—	nA	
	• 4 MHz	_	200	—	μA	
	• 8 MHz (RANGE=01)	_	300	—	μA	
	• 16 MHz	_	950	—	μA	
		_	1.2	_	mA	

Table 19. Oscillator DC electrical specifications

Table continues on the next page ...



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	• 24 MHz	_	1.5	—	mA	
	• 32 MHz					
I <sub>DDOSC</sub>	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	_	μA	
	• 4 MHz	—	400	_	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C <sub>x</sub>	EXTAL load capacitance		_	_		2, 3
Cy	XTAL load capacitance	_				2, 3
R <sub>F</sub>	Feedback resistor — low-frequency, low-power mode (HGO=0)	_	_	_	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	_	_	_	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	_	1	_	MΩ	
R <sub>S</sub>	Series resistor — low-frequency, low-power mode (HGO=0)	_	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200		kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	_	_	_	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)					
		—	0	_	kΩ	
V <sub>pp</sub> <sup>5</sup>	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	_	0.6	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	_	V <sub>DD</sub>	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)		0.6		V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)		V <sub>DD</sub>		V	

Table 19.	<b>Oscillator DC electrical s</b>	pecifications (	(continued)	1
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V<sub>DD</sub>=3.3 V, Temperature =25 °C
 See crystal or resonator manufacturer's recommendation



### 3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t <sub>hvpgm4</sub>	Longword Program high-voltage time	_	7.5	18	μs	
t <sub>hversscr</sub>	Sector Erase high-voltage time	_	13	113	ms	1
t <sub>hversall</sub>	Erase All high-voltage time	_	52	452	ms	1

Table 21. NVM program/erase timing specifications

1. Maximum time based on expectations at cycling end-of-life.

#### 3.4.1.2 Flash timing specifications — commands Table 22. Flash command timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t <sub>rd1sec1k</sub>	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t <sub>pgmchk</sub>	Program Check execution time	—	—	45	μs	1
t <sub>rdrsrc</sub>	Read Resource execution time	—	—	30	μs	1
t <sub>pgm4</sub>	Program Longword execution time	—	65	145	μs	_
t <sub>ersscr</sub>	Erase Flash Sector execution time	—	14	114	ms	2
t <sub>rd1all</sub>	Read 1s All Blocks execution time	_	—	1.8	ms	_
t <sub>rdonce</sub>	Read Once execution time	_	—	25	μs	1
t <sub>pgmonce</sub>	Program Once execution time	—	65	—	μs	_
t <sub>ersall</sub>	Erase All Blocks execution time	—	88	650	ms	2
t <sub>vfykey</sub>	Verify Backdoor Access Key execution time	—	—	30	μs	1

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

### 3.4.1.3 Flash high voltage current behaviors Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I <sub>DD_PGM</sub>	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I <sub>DD_ERS</sub>	Average current adder during high voltage flash erase operation		1.5	4.0	mA



### 3.4.1.4 Reliability specifications Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
	Program	m Flash				
t <sub>nvmretp10k</sub>	Data retention after up to 10 K cycles	5	50	_	years	_
t <sub>nvmretp1k</sub>	Data retention after up to 1 K cycles	20	100	_	years	_
n <sub>nvmcycp</sub>	Cycling endurance	10 K	50 K	_	cycles	2

 Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40 °C  $\leq$  T<sub>i</sub>  $\leq$  125 °C.

## 3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

## 3.6 Analog

## 3.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

### 3.6.1.1 12-bit ADC operating conditions Table 25. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage	Absolute		—	3.6	V	—
$\Delta V_{DDA}$	Supply voltage	Delta to $V_{DD}$ ( $V_{DD} - V_{DDA}$ )	-100	0	+100	mV	2
$\Delta V_{SSA}$	Ground voltage	Delta to $V_{SS}$ ( $V_{SS} - V_{SSA}$ )	-100	0	+100	mV	2
V <sub>REFH</sub>	ADC reference voltage high		1.13	V <sub>DDA</sub>	V <sub>DDA</sub>	V	3
V <sub>REFL</sub>	ADC reference voltage low		V <sub>SSA</sub>	V <sub>SSA</sub>	V <sub>SSA</sub>	V	3
V <sub>ADIN</sub>	Input voltage		V <sub>REFL</sub>	_	V <sub>REFH</sub>	V	_
C <sub>ADIN</sub>	Input capacitance	8-bit / 10-bit / 12-bit modes	—	4	5	pF	
R <sub>ADIN</sub>	Input series resistance		_	2	5	kΩ	_

Table continues on the next page...



Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
R <sub>AS</sub>	Analog source resistance (external)	12-bit modes f <sub>ADCK</sub> < 4 MHz	_	_	5	kΩ	4
f <sub>ADCK</sub>	ADC conversion clock frequency	≤ 12-bit mode	1.0	_	18.0	MHz	5
C <sub>rate</sub>	ADC conversion rate	<ul> <li>≤ 12-bit modes</li> <li>No ADC hardware averaging</li> <li>Continuous conversions enabled, subsequent conversion time</li> </ul>	20.000	_	818.330	Ksps	6

- 1. Typical values assume  $V_{DDA}$  = 3.0 V, Temp = 25 °C,  $f_{ADCK}$  = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
- 2. DC potential difference.
- For packages without dedicated VREFH and VREFL pins, V<sub>REFH</sub> is internally tied to V<sub>DDA</sub>, and V<sub>REFL</sub> is internally tied to V<sub>SSA</sub>.
- 4. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R<sub>AS</sub>/C<sub>AS</sub> time constant should be kept to < 1 ns.</p>
- 5. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
- 6. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.



Figure 7. ADC input impedance equivalency diagram



#### 12-bit ADC electrical characteristics 3.6.1.2

Symbol	Description	Conditions <sup>1</sup>	Min.	Typ. <sup>2</sup>	Max.	Unit	Notes
I <sub>DDA_ADC</sub>	Supply current		0.215	_	1.7	mA	3
	ADC	• ADLPC = 1, ADHSC =	1.2	2.4	3.9	MHz	t <sub>ADACK</sub> =
	asynchronous	0	2.4	4.0	6.1	MHz	1/f <sub>ADACK</sub>
		<ul> <li>ADLPC = 1, ADHSC =</li> <li>1</li> </ul>	3.0	5.2	7.3	MHz	
fadack		• ADLPC = 0, ADHSC = 0	4.4	6.2	9.5	MHz	
		• ADLPC = 0, ADHSC = 1					
	Sample Time	See Reference Manual chapte	r for sample	times			
TUE	Total unadjusted	12-bit modes	—	±4	±6.8	LSB <sup>4</sup>	5
	error	12-bit modes	_	±1.4	±2.1		
DNL	Differential non- linearity	12-bit modes		±0.7	-1.1 to +1.9	LSB <sup>4</sup>	5
		12-bit modes		±0.2	-0.3 to 0.5		
INL	Integral non- linearity	12-bit modes		±1.0	-2.7 to +1.9	LSB <sup>4</sup>	5
		<ul> <li>&lt;12-bit modes</li> </ul>	_	±0.5	–0.7 to +0.5		
E <sub>FS</sub>	Full-scale error	12-bit modes	—	-4	-5.4	LSB <sup>4</sup>	V <sub>ADIN</sub> =
		<ul> <li>&lt;12-bit modes</li> </ul>	_	-1.4	-1.8		V <sub>DDA</sub> <sup>5</sup>
EQ	Quantization error	12-bit modes	_	—	±0.5	LSB <sup>4</sup>	
E <sub>IL</sub>	Input leakage error			$I_{ln} \times R_{AS}$		mV	I <sub>In</sub> = leakage current
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	6
V <sub>TEMP25</sub>	Temp sensor voltage	25 °C	706	716	726	mV	6

## Table 26. 12-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ , $V_{REFL} = V_{SSA}$ )

1. All accuracy numbers assume the ADC is calibrated with  $V_{REFH} = V_{DDA}$ 2. Typical values assume  $V_{DDA} = 3.0 \text{ V}$ , Temp = 25 °C,  $f_{ADCK} = 2.0 \text{ MHz}$  unless otherwise stated. Typical values are for reference only and are not tested in production.



Symbol	Description	Min.	Тур.	Max.	Unit
V <sub>CMPOI</sub>	Output low	—	—	0.5	V
t <sub>DHS</sub>	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
t <sub>DLS</sub>	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns
	Analog comparator initialization delay <sup>2</sup>	_	—	40	μs
I <sub>DAC6b</sub>	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB <sup>3</sup>
DNL	6-bit DAC differential non-linearity	-0.3	_	0.3	LSB

 Table 27. Comparator and 6-bit DAC electrical specifications (continued)

1. Typical hysteresis is measured with input voltage range limited to 0.7 to  $V_{\text{DD}}$  – 0.7 V.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (writes to

DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

3.  $1 \text{ LSB} = V_{\text{reference}}/64$ 



Figure 9. Typical hysteresis vs. Vin level ( $V_{DD} = 3.3 V$ , PMODE = 0)





Figure 10. Typical hysteresis vs. Vin level ( $V_{DD}$  = 3.3 V, PMODE = 1)

## 3.7 Timers

See General switching specifications.

## 3.8 Communication interfaces

## 3.8.1 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to  $20\% V_{DD}$  and  $80\% V_{DD}$  thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f <sub>op</sub>	Frequency of operation	f <sub>periph</sub> /2048	f <sub>periph</sub> /2	Hz	1

Table 28. SPI master mode timing on slew rate disabled pads

Table continues on the next page ...



Characteristic	Symbol	Standa	rd Mode	Fast	Mode	Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f <sub>SCL</sub>	0	100	0	400 <sup>1</sup>	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t <sub>HD</sub> ; STA	4	—	0.6	—	μs
LOW period of the SCL clock	t <sub>LOW</sub>	4.7	—	1.3	—	μs
HIGH period of the SCL clock	t <sub>HIGH</sub>	4	—	0.6	—	μs
Set-up time for a repeated START condition	t <sub>SU</sub> ; STA	4.7	_	0.6	—	μs
Data hold time for I <sup>2</sup> C bus devices	t <sub>HD</sub> ; DAT	0 <sup>2</sup>	3.45 <sup>3</sup>	04	0.9 <sup>2</sup>	μs
Data set-up time	t <sub>SU</sub> ; DAT	250 <sup>5</sup>	—	100 <sup>3</sup> , <sup>6</sup>	—	ns
Rise time of SDA and SCL signals	t <sub>r</sub>	_	1000	20 +0.1C <sub>b</sub> <sup>7</sup>	300	ns
Fall time of SDA and SCL signals	t <sub>f</sub>	_	300	20 +0.1C <sub>b</sub> <sup>6</sup>	300	ns
Set-up time for STOP condition	t <sub>SU</sub> ; STO	4	—	0.6	—	μs
Bus free time between STOP and START condition	t <sub>BUF</sub>	4.7	_	1.3	—	μs
Pulse width of spikes that must be suppressed by the input filter	t <sub>SP</sub>	N/A	N/A	0	50	ns

### 3.8.2 Inter-Integrated Circuit Interface (I2C) timing Table 32. I2C timing

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only achieved when using the High drive pins (see Voltage and current operating behaviors) or when using the Normal drive pins and VDD ≥ 2.7 V

The master mode I<sup>2</sup>C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves
acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL
lines.

- 3. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
- 4. Input signal Slew = 10 ns and Output Load = 50 pF
- 5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
- 6. A Fast mode I<sup>2</sup>C bus device can be used in a Standard mode I2C bus system, but the requirement  $t_{SU; DAT} \ge 250$  ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line  $t_{rmax} + t_{SU; DAT} = 1000 + 250 = 1250$  ns (according to the Standard mode I<sup>2</sup>C bus specification) before the SCL line is released.
- 7.  $C_b$  = total capacitance of the one bus line in pF.



Figure 15. Timing definition for fast and standard mode devices on the I<sup>2</sup>C bus



80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
6	_	_	_	PTE5	DISABLED		PTE5						
7	3	1	_	VDD	VDD	VDD							
8	4	2	_	VSS	VSS	VSS							
9	5	3	3	PTE16	ADC0_SE1	ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_ CLKIN0			
10	6	4	4	PTE17	ADC0_SE5a	ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_ CLKIN1		LPTMR0_ ALT3	
11	7	5	5	PTE18	ADC0_SE2	ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		
12	8	6	6	PTE19	ADC0_SE6a	ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI		
13	9	7	-	PTE20	ADC0_SE0	ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
14	10	8	-	PTE21	ADC0_SE4a	ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
15	11	Ι	-	PTE22	ADC0_SE3	ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
16	12	Ι	-	PTE23	ADC0_SE7a	ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
17	13	9	7	VDDA	VDDA	VDDA							
18	14	10	_	VREFH	VREFH	VREFH							
19	15	11	_	VREFL	VREFL	VREFL							
20	16	12	8	VSSA	VSSA	VSSA							
21	17	13	_	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_ CLKIN0			
22	18	14	9	PTE30	ADC0_SE23/ CMP0_IN4	ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_ CLKIN1			
23	19	—	_	PTE31	DISABLED		PTE31		TPM0_CH4				
24	20	15	—	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
25	21	16	_	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
26	22	17	10	PTA0	SWD_CLK		PTA0		TPM0_CH5				SWD_CLK
27	23	18	11	PTA1	DISABLED		PTA1	UART0_RX	TPM2_CH0				
28	24	19	12	PTA2	DISABLED		PTA2	UART0_TX	TPM2_CH1				
29	25	20	13	PTA3	SWD_DIO		PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
30	26	21	14	PTA4	NMI_b		PTA4	I2C1_SDA	TPM0_CH1				NMI_b
31	27	Ι	-	PTA5	DISABLED		PTA5		TPM0_CH2				
32	28	Ι	-	PTA12	DISABLED		PTA12		TPM1_CH0				
33	29	-	-	PTA13	DISABLED		PTA13		TPM1_CH1				
34	_	_	_	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX				
35	-	-	_	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX				
36	_	-	_	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO		
37	-	-	-	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI		
38	30	22	15	VDD	VDD	VDD							
39	31	23	16	VSS	VSS	VSS							
40	32	24	17	PTA18	EXTAL0	EXTAL0	PTA18		UART1_RX	TPM_ Clkino			

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
41	33	25	18	PTA19	XTAL0	XTAL0	PTA19		UART1_TX	TPM_ CLKIN1		LPTMR0_ ALT1	
42	34	26	19	RESET_b	RESET_b		PTA20						
43	35	27	20	PTB0/ LLWU_P5	ADC0_SE8	ADC0_SE8	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
44	36	28	21	PTB1	ADC0_SE9	ADC0_SE9	PTB1	I2C0_SDA	TPM1_CH1				
45	37	29	-	PTB2	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	TPM2_CH0				
46	38	30	_	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	TPM2_CH1				
47	_	_	_	PTB8	DISABLED		PTB8		EXTRG_IN				
48	_	-	_	PTB9	DISABLED		PTB9						
49	_	_	_	PTB10	DISABLED		PTB10	SPI1_PCS0					
50	_	-	-	PTB11	DISABLED		PTB11	SPI1_SCK					
51	39	31	_	PTB16	DISABLED		PTB16	SPI1_MOSI	UART0_RX	TPM_ CLKIN0	SPI1_MISO		
52	40	32	1	PTB17	DISABLED		PTB17	SPI1_MISO	UART0_TX	TPM_ CLKIN1	SPI1_MOSI		
53	41	—	—	PTB18	DISABLED		PTB18		TPM2_CH0				
54	42	_	-	PTB19	DISABLED		PTB19		TPM2_CH1				
55	43	33	-	PTC0	ADC0_SE14	ADC0_SE14	PTC0		EXTRG_IN		CMP0_OUT		
56	44	34	22	PTC1/ LLWU_P6/ RTC_CLKIN	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0			
57	45	35	23	PTC2	ADC0_SE11	ADC0_SE11	PTC2	I2C1_SDA		TPM0_CH1			
58	46	36	24	PTC3/ LLWU_P7	DISABLED		PTC3/ LLWU_P7		UART1_RX	TPM0_CH2	CLKOUT		
59	47	—	—	VSS	VSS	VSS							
60	48	-	_	VDD	VDD	VDD							
61	49	37	25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	TPM0_CH3			
62	50	38	26	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2			CMP0_OUT	
63	51	39	27	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_MOSI	EXTRG_IN		SPI0_MISO		
64	52	40	28	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_MISO			SPI0_MOSI		
65	53	Ι	-	PTC8	CMP0_IN2	CMP0_IN2	PTC8	I2C0_SCL	TPM0_CH4				
66	54	-	-	PTC9	CMP0_IN3	CMP0_IN3	PTC9	I2C0_SDA	TPM0_CH5				
67	55	-	-	PTC10	DISABLED		PTC10	I2C1_SCL					
68	56	-	-	PTC11	DISABLED		PTC11	I2C1_SDA					
69	-	—	—	PTC12	DISABLED		PTC12			TPM_ CLKIN0			
70	-	-	-	PTC13	DISABLED		PTC13			TPM_ CLKIN1			
71	-	-	-	PTC16	DISABLED		PTC16						

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Figure 16. KL14 80-pin LQFP pinout diagram





Figure 17. KL14 64-pin LQFP pinout diagram





Figure 18. KL14 48-pin QFN pinout diagram





Figure 19. KL14 32-pin QFN pinout diagram

## 6 Ordering parts

## 6.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to **freescale.com** and perform a part number search for the following device numbers: PKL14 and MKL14

## 7 Part identification